Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	168MHz
Connectivity	CANbus, DCMI, EBI/EMI, Ethernet, I²C, IrDA, LINbus, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, I²S, LCD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	192K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f407vgt7

2 Description

The STM32F405xx and STM32F407xx family is based on the high-performance ARM® Cortex®-M4 32-bit RISC core operating at a frequency of up to 168 MHz. The Cortex-M4 core features a Floating point unit (FPU) single precision which supports all ARM single-precision data-processing instructions and data types. It also implements a full set of DSP instructions and a memory protection unit (MPU) which enhances application security.

The STM32F405xx and STM32F407xx family incorporates high-speed embedded memories (Flash memory up to 1 Mbyte, up to 192 Kbytes of SRAM), up to 4 Kbytes of backup SRAM, and an extensive range of enhanced I/Os and peripherals connected to two APB buses, three AHB buses and a 32-bit multi-AHB bus matrix.

All devices offer three 12-bit ADCs, two DACs, a low-power RTC, twelve general-purpose 16-bit timers including two PWM timers for motor control, two general-purpose 32-bit timers. a true random number generator (RNG). They also feature standard and advanced communication interfaces.

- Up to three I^2Cs
- Three SPIs, two I^2Ss full duplex. To achieve audio class accuracy, the I2S peripherals can be clocked via a dedicated internal audio PLL or via an external clock to allow synchronization.
- Four USARTs plus two UARTs
- An USB OTG full-speed and a USB OTG high-speed with full-speed capability (with the ULPI),
- Two CANs
- An SDIO/MMC interface
- Ethernet and the camera interface available on STM32F407xx devices only.

New advanced peripherals include an SDIO, an enhanced flexible static memory control (FSMC) interface (for devices offered in packages of 100 pins and more), a camera interface for CMOS sensors. Refer to *Table 2: STM32F405xx and STM32F407xx: features and peripheral counts* for the list of peripherals available on each part number.

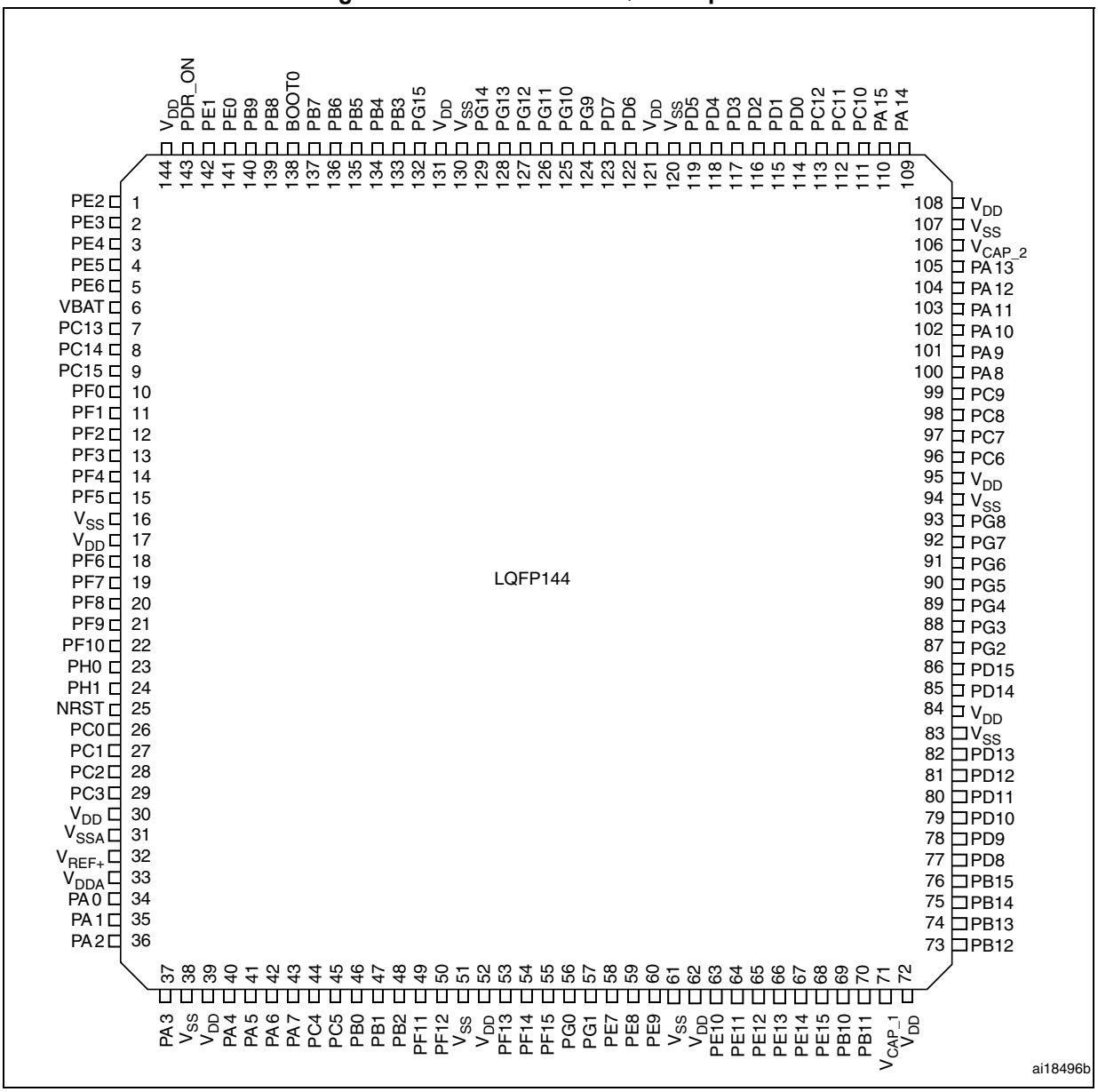
The STM32F405xx and STM32F407xx family operates in the –40 to +105 °C temperature range from a 1.8 to 3.6 V power supply. The supply voltage can drop to 1.7 V when the device operates in the 0 to 70 °C temperature range using an external power supply supervisor: refer to *Section : Internal reset OFF*. A comprehensive set of power-saving mode allows the design of low-power applications.

The STM32F405xx and STM32F407xx family offers devices in various packages ranging from 64 pins to 176 pins. The set of included peripherals changes with the device chosen.

These features make the STM32F405xx and STM32F407xx microcontroller family suitable for a wide range of applications:

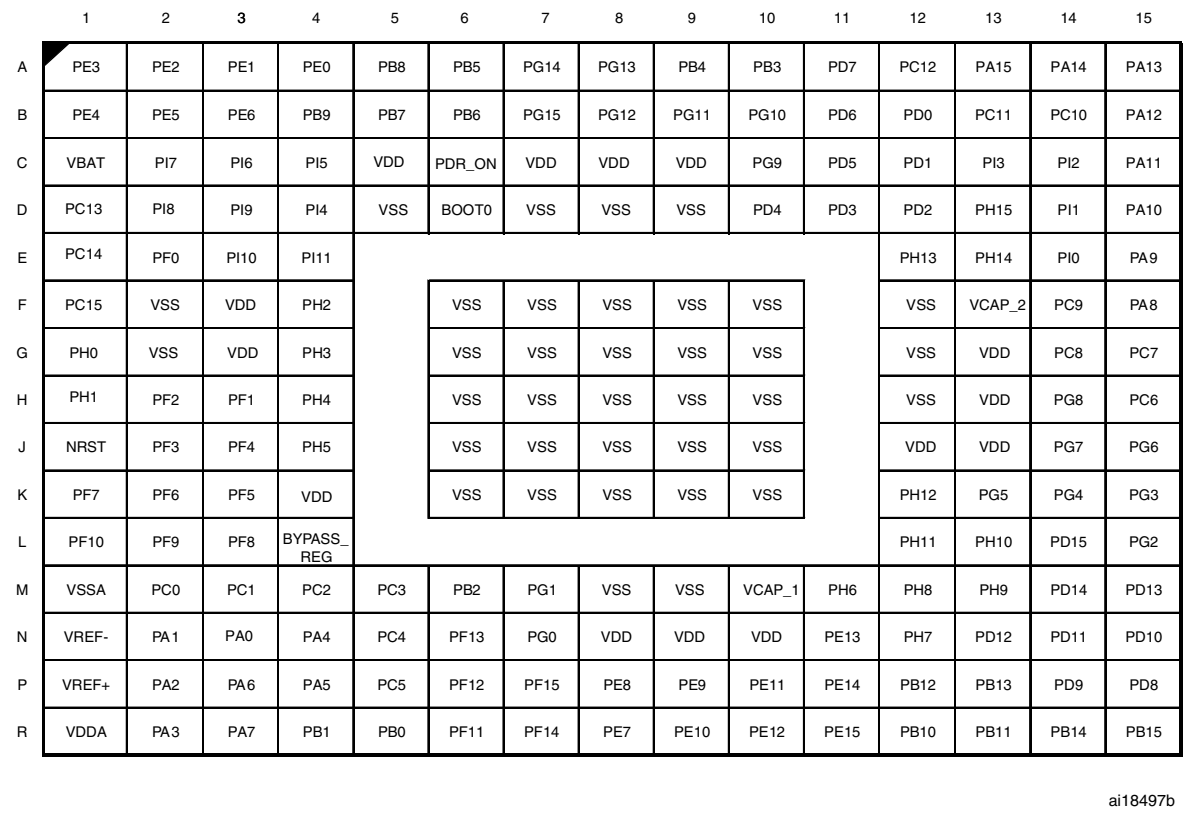
- Motor drive and application control
- Medical equipment
- Industrial applications: PLC, inverters, circuit breakers
- Printers, and scanners
- Alarm systems, video intercom, and HVAC
- Home audio appliances

Figure 14. STM32F40xxx LQFP144 pinout



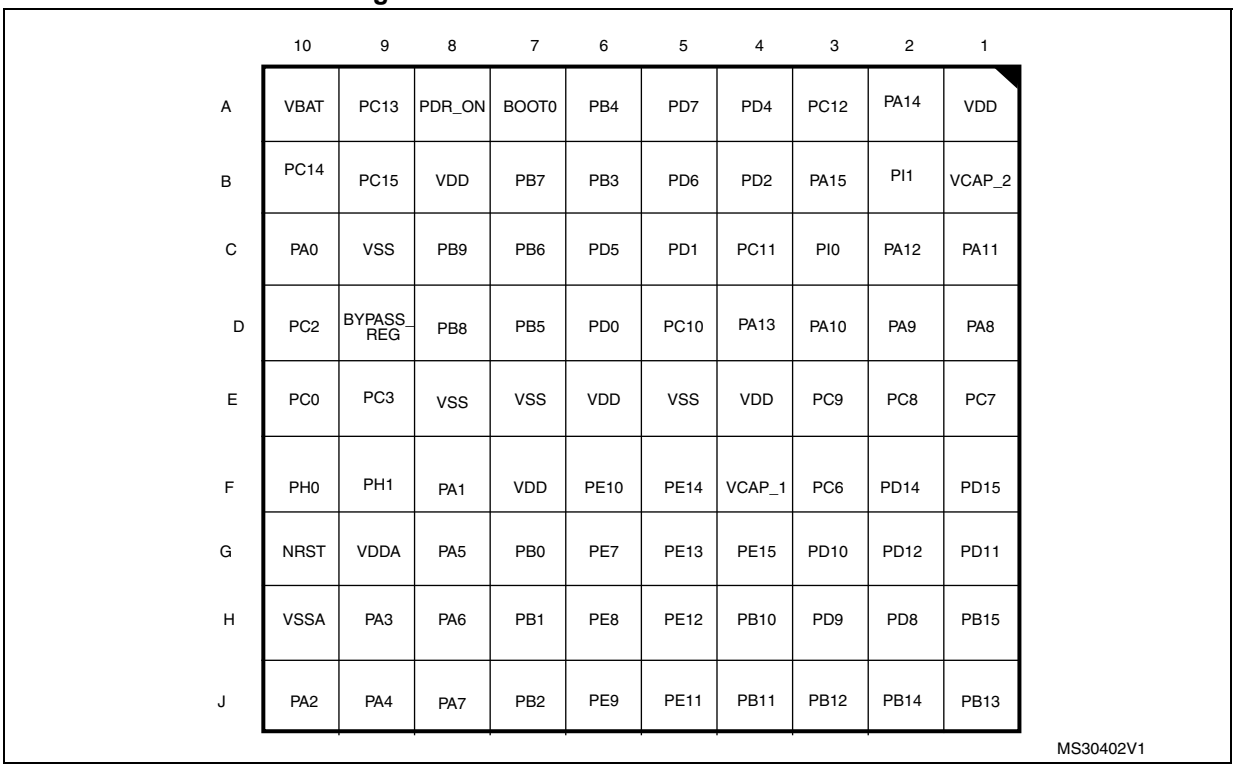
1. The above figure shows the package top view.

Figure 16. STM32F40xxx UFBGA176 ballout



1. This figure shows the package top view.

Figure 17. STM32F40xxx WLCSP90 ballout



1. This figure shows the package bump view.

Table 6. Legend/abbreviations used in the pinout table

Name	Abbreviation	Definition
Pin name	Unless otherwise specified in brackets below the pin name, the pin function during and after reset is the same as the actual pin name	
Pin type	S	Supply pin
	I	Input only pin
	I/O	Input / output pin
I/O structure	FT	5 V tolerant I/O
	TTa	3.3 V tolerant I/O directly connected to ADC
	B	Dedicated BOOT0 pin
	RST	Bidirectional reset pin with embedded weak pull-up resistor
Notes	Unless otherwise specified by a note, all I/Os are set as floating inputs during and after reset	
Alternate functions	Functions selected through GPIOx_AFR registers	
Additional functions	Functions directly selected/enabled through peripheral registers	

Table 7. STM32F40xxx pin and ball definitions (continued)

Pin number						Pin name (function after reset)[1]	Pin type	I / O structure	Notes	Alternate functions	Additional functions
LQFP64	WLCSP90	LQFP100	LQFP144	UFBGA176	LQFP176						
-	-	-	-	C14	133	PI2	I/O	FT	-	TIM8_CH4 /SPI2_MISO / DCMI_D9 / I2S2ext_SD/ EVENTOUT	-
-	-	-	-	C13	134	PI3	I/O	FT		TIM8_ETR / SPI2_MOSI / I2S2_SD / DCMI_D10/ EVENTOUT	-
-	-	-	-	D9	135	V_{SS}	S	-	-	-	-
-	-	-	-	C9	136	V_{DD}	S	-	-	-	-
49	A2	76	109	A14	137	PA14 (JTCK/SWCLK)	I/O	FT	-	JTCK-SWCLK/ EVENTOUT	-
50	B3	77	110	A13	138	PA15 (JTDI)	I/O	FT	-	JTDI/ SPI3_NSS/ I2S3_WS/TIM2_CH1_ETR / SPI1_NSS / EVENTOUT	-
51	D5	78	111	B14	139	PC10	I/O	FT	-	SPI3_SCK / I2S3_CK/ UART4_TX/SDIO_D2 / DCMI_D8 / USART3_TX/ EVENTOUT	-
52	C4	79	112	B13	140	PC11	I/O	FT	-	UART4_RX/ SPI3_MISO / SDIO_D3 / DCMI_D4/USART3_RX / I2S3ext_SD/ EVENTOUT	-
53	A3	80	113	A12	141	PC12	I/O	FT	-	UART5_TX/SDIO_CK / DCMI_D9 / SPI3_MOSI /I2S3_SD / USART3_CK/ EVENTOUT	-
-	D6	81	114	B12	142	PD0	I/O	FT	-	FSMC_D2/CAN1_RX/ EVENTOUT	-
-	C5	82	115	C12	143	PD1	I/O	FT	-	FSMC_D3 / CAN1_TX/ EVENTOUT	-
54	B4	83	116	D12	144	PD2	I/O	FT	-	TIM3_ETR/UART5_RX/ SDIO_CMD / DCMI_D11/ EVENTOUT	-
-	-	84	117	D11	145	PD3	I/O	FT	-	FSMC_CLK/ USART2_CTS/ EVENTOUT	-

Table 9. Alternate function mapping

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/SPI2/I2S2/I2S2ext	SPI3/I2Sext/I2S3	USART1/2/3/I2S3ext	UART4/5/USART6	CAN1/2 TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/OTG_FS	DCMI		
Port A	PA0	-	TIM2_CH1_ETR	TIM 5_CH1	TIM8_ETR	-	-	-	USART2_CTS	UART4_TX	-	-	ETH_MII_CRS	-	-	-	EVENTOUT
	PA1	-	TIM2_CH2	TIM5_CH2	-	-	-	-	USART2_RTS	UART4_RX	-	-	ETH_MII_RX_CLK ETH_RMII__REF_CLK	-	-	-	EVENTOUT
	PA2	-	TIM2_CH3	TIM5_CH3	TIM9_CH1	-	-	-	USART2_TX	-	-	-	ETH_MDIO	-	-	-	EVENTOUT
	PA3	-	TIM2_CH4	TIM5_CH4	TIM9_CH2	-	-	-	USART2_RX	-	-	OTG_HS_ULPI_D0	ETH _MII_COL	-	-	-	EVENTOUT
	PA4	-	-	-	-	-	SPI1_NSS	SPI3_NSS I2S3_WS	USART2_CK	-	-	-	-	OTG_HS_SOF	DCMI_HSYNC	-	EVENTOUT
	PA5	-	TIM2_CH1_ETR	-	TIM8_CH1N	-	SPI1_SCK	-	-	-	-	OTG_HS_ULPI_CK	-	-	-	-	EVENTOUT
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	-	SPI1_MISO	-	-	-	TIM13_CH1	-	-	-	DCMI_PIXCK	-	EVENTOUT
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	-	SPI1_MOSI	-	-	-	TIM14_CH1	-	ETH_MII_RX_DV ETH_RMII_CRS_DV	-	-	-	EVENTOUT
	PA8	MCO1	TIM1_CH1	-	-	I2C3_SCL	-	-	USART1_CK	-	-	OTG_FS_SOF	-	-	-	-	EVENTOUT
	PA9	-	TIM1_CH2	-	-	I2C3_SMBA	-	-	USART1_TX	-	-	-	-	-	DCMI_D0	-	EVENTOUT
	PA10	-	TIM1_CH3	-	-	-	-	-	USART1_RX	-	-	OTG_FS_ID	-	-	DCMI_D1	-	EVENTOUT
	PA11	-	TIM1_CH4	-	-	-	-	-	USART1_CTS	-	CAN1_RX	OTG_FS_DM	-	-	-	-	EVENTOUT
	PA12	-	TIM1_ETR	-	-	-	-	-	USART1_RTS	-	CAN1_TX	OTG_FS_DP	-	-	-	-	EVENTOUT
	PA13	JTMS-SWDIO	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA14	JTCK-SWCLK	-	-	-	-	-	-	-	-	-	-	-	-	-	-	EVENTOUT
	PA15	JTDI	TIM 2_CH1 TIM 2_ETR	-	-	-	SPI1_NSS	SPI3_NSS/I2S3_WS	-	-	-	-	-	-	-	-	EVENTOUT

Table 9. Alternate function mapping (continued)

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7	AF8	AF9	AF10	AF11	AF12	AF13	AF14	AF15
		SYS	TIM1/2	TIM3/4/5	TIM8/9/10/11	I2C1/2/3	SPI1/SPI2/I2S2/I2S2ext	SPI3/I2Sext/I2S3	USART1/2/3/I2S3ext	UART4/5/USART6	CAN1/2 TIM12/13/14	OTG_FS/OTG_HS	ETH	FSMC/SDIO/OTG_FS	DCMI		
Port F	PF0	-	-	-	-	I2C2_SDA	-	-	-	-	-	-	-	FSMC_A0	-	-	EVENTOUT
	PF1	-	-	-	-	I2C2_SCL	-	-	-	-	-	-	-	FSMC_A1	-	-	EVENTOUT
	PF2	-	-	-	-	I2C2_SMBA	-	-	-	-	-	-	-	FSMC_A2	-	-	EVENTOUT
	PF3	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A3	-	-	EVENTOUT
	PF4	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A4	-	-	EVENTOUT
	PF5	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A5	-	-	EVENTOUT
	PF6	-	-	-	TIM10_CH1	-	-	-	-	-	-	-	-	FSMC_NIORD	-	-	EVENTOUT
	PF7	-	-	-	TIM11_CH1	-	-	-	-	-	-	-	-	FSMC_NREG	-	-	EVENTOUT
	PF8	-	-	-	-	-	-	-	-	-	TIM13_CH1	-	-	FSMC_NIOWR	-	-	EVENTOUT
	PF9	-	-	-	-	-	-	-	-	-	TIM14_CH1	-	-	FSMC_CD	-	-	EVENTOUT
	PF10	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_INTR	-	-	EVENTOUT
	PF11	-	-	-	-	-	-	-	-	-	-	-	-		DCMI_D12	-	EVENTOUT
	PF12	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A6	-	-	EVENTOUT
	PF13	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A7	-	-	EVENTOUT
	PF14	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A8	-	-	EVENTOUT
	PF15	-	-	-	-	-	-	-	-	-	-	-	-	FSMC_A9	-	-	EVENTOUT

Table 12. Current characteristics

Symbol	Ratings	Max.	Unit
I_{VDD}	Total current into V_{DD} power lines (source)(1)	240	mA
I_{VSS}	Total current out of V_{SS} ground lines (sink)(1)	240	
I_{IO}	Output current sunk by any I/O and control pin	25	
	Output current source by any I/Os and control pin	25	
$I_{INJ(PIN)}$ (2)	Injected current on five-volt tolerant I/O(3)	–5/+0	
	Injected current on any other pin(4)	±5	
$\Sigma I_{INJ(PIN)}$(4)	Total injected current (sum of all I/O and control pins)(5)	±25	

1. All main power (V_{DD}, V_{DDA}) and ground (V_{SS}, V_{SSA}) pins must always be connected to the external power supply, in the permitted range.
2. Negative injection disturbs the analog performance of the device. See note in *Section 5.3.21: 12-bit ADC characteristics*.
3. Positive injection is not possible on these I/Os. A negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
4. A positive injection is induced by $V_{IN}>V_{DD}$ while a negative injection is induced by $V_{IN}<V_{SS}$. $I_{INJ(PIN)}$ must never be exceeded. Refer to *Table 11* for the values of the maximum allowed input voltage.
5. When several inputs are submitted to a current injection, the maximum $\Sigma I_{INJ(PIN)}$ is the absolute sum of the positive and negative injected currents (instantaneous values).

Table 13. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	–65 to +150	°C
T_J	Maximum junction temperature	125	°C

5.3 Operating conditions

5.3.1 General operating conditions

Table 14. General operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{HCLK}	Internal AHB clock frequency	VOS bit in PWR_CR register = 0(1)	0	-	144	MHz
		VOS bit in PWR_CR register= 1	0	-	168	
f_{PCLK1}	Internal APB1 clock frequency	-	0	-	42	
f_{PCLK2}	Internal APB2 clock frequency	-	0	-	84	
V_{DD}	Standard operating voltage	-	1.8(2)	-	3.6	V
V_{DDA}(3)(4)	Analog operating voltage (ADC limited to 1.2 M samples)	Must be the same potential as V_{DD}(5)	1.8(2)	-	2.4	V
	Analog operating voltage (ADC limited to 1.4 M samples)		2.4	-	3.6	
V_{BAT}	Backup operating voltage	-	1.65	-	3.6	V

Table 28. Peripheral current consumption (continued)

Peripheral		I_{DD}(Typ)(1)		Unit
		Scale1 (up t 168 MHz)	Scale2 (up to 144 MHz)	
AHB2 (up to 168 MHz)	OTG_FS	26.45	26.67	µA/MHz
	DCMI	5.87	5.35	
	RNG	1.50	1.67	
AHB3 (up to 168 MHz)	FSMC	12.46	11.31	µA/MHz
Bus matrix(2)		13.10	11.81	µA/MHz
APB1 (up to 42 MHz)	TIM2	16.71	16.50	µA/MHz
	TIM3	12.33	11.94	
	TIM4	13.45	12.92	
	TIM5	17.14	16.58	
	TIM6	2.43	3.06	
	TIM7	2.43	2.22	
	TIM12	6.62	6.83	
	TIM13	5.05	5.47	
	TIM14	5.26	5.61	
	PWR	1.00	0.56	
	USART2	2.69	2.78	
	USART3	2.74	2.78	
	UART4	3.24	3.33	
	UART5	2.69	2.78	
	I2C1	2.67	2.50	
	I2C2	2.83	2.78	
	I2C3	2.81	2.78	
	SPI2	2.43	2.22	
	SPI3	2.43	2.22	
	I2S2(3)	2.43	2.22	
	I2S3(3)	2.26	2.22	
	CAN1	5.12	5.56	
	CAN2	4.81	5.28	
	DAC(4)	1.67	1.67	
	WWDG	1.00	0.83	

A device reset allows normal operations to be resumed.

The test results are given in *Table 43*. They are based on the EMS levels and classes defined in application note AN1709.

Table 43. EMS characteristics

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD} = 3.3 V, LQFP176, T_A = +25 °C, f_{HCLK} = 168 MHz, conforms to IEC 61000-4-2	2B
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD} = 3.3 V, LQFP176, T_A = +25 °C, f_{HCLK} = 168 MHz, conforms to IEC 61000-4-2	4A

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical Data corruption (control registers...)

Prequalification trials

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the NRST pin or the Oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Input/output AC characteristics

The definition and values of input/output AC characteristics are given in *Figure 37* and *Table 50*, respectively.

Unless otherwise specified, the parameters given in *Table 50* are derived from tests performed under the ambient temperature and V_{DD} supply voltage conditions summarized in *Table 14*.

Table 50. I/O AC characteristics(1)(2)

OSPEEDRy [1:0] bit value(1)	Symbol	Parameter	Conditions	Min	Typ	Max	Unit
00	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} > 2.70 V	-	-	4	MHz
			C_L = 50 pF, V_{DD} > 1.8 V	-	-	2	
			C_L = 10 pF, V_{DD} > 2.70 V	-	-	8	
			C_L = 10 pF, V_{DD} > 1.8 V	-	-	4	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} = 1.8 V to 3.6 V	-	-	100	ns
01	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 50 pF, V_{DD} > 2.70 V	-	-	25	MHz
			C_L = 50 pF, V_{DD} > 1.8 V	-	-	12.5	
			C_L = 10 pF, V_{DD} > 2.70 V	-	-	50(4)	
			C_L = 10 pF, V_{DD} > 1.8 V	-	-	20	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 50 pF, V_{DD} >2.7 V	-	-	10	ns
			C_L = 50 pF, V_{DD} > 1.8 V	-	-	20	
			C_L = 10 pF, V_{DD} > 2.70 V	-	-	6	
			C_L = 10 pF, V_{DD} > 1.8 V	-	-	10	
10	$f_{max(IO)out}$	Maximum frequency(3)	C_L = 40 pF, V_{DD} > 2.70 V	-	-	50(4)	MHz
			C_L = 40 pF, V_{DD} > 1.8 V	-	-	25	
			C_L = 10 pF, V_{DD} > 2.70 V	-	-	100(4)	
			C_L = 10 pF, V_{DD} > 1.8 V	-	-	50(4)	
	$t_{f(IO)out}$/ $t_{r(IO)out}$	Output high to low level fall time and output low to high level rise time	C_L = 40 pF, V_{DD} > 2.70 V	-	-	6	ns
			C_L = 40 pF, V_{DD} > 1.8 V	-	-	10	
			C_L = 10 pF, V_{DD} > 2.70 V	-	-	4	
			C_L = 10 pF, V_{DD} > 1.8 V	-	-	6	

Figure 44. USB OTG FS timings: definition of data signal rise and fall time

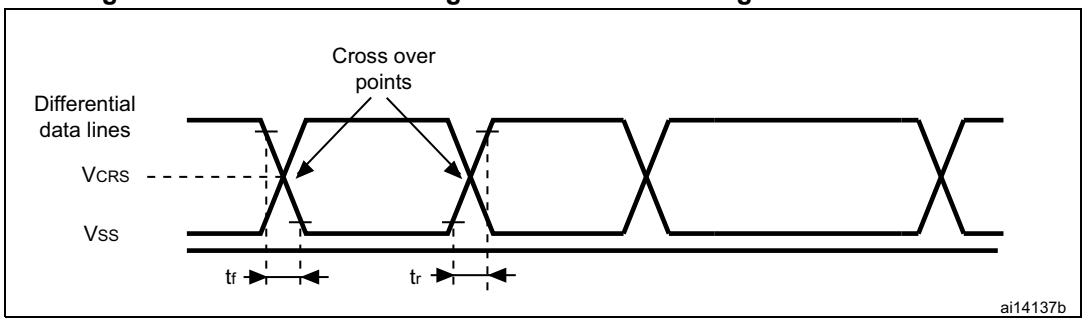


Table 59. USB OTG FS electrical characteristics(1)

Driver characteristics					
Symbol	**Parameter**	**Conditions**	**Min**	**Max**	**Unit**
t_r	Rise time(2)	C_L = 50 pF	4	20	ns
t_f	Fall time(2)	C_L = 50 pF	4	20	ns
t_{rfm}	Rise/ fall time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal crossover voltage	-	1.3	2.0	V

1. Guaranteed by design.
2. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

USB HS characteristics

Unless otherwise specified, the parameters given in *Table 62* for ULPI are derived from tests performed under the ambient temperature, f_{HCLK} frequency summarized in *Table 61* and V_{DD} supply voltage conditions summarized in *Table 60*, with the following configuration:

- Output speed is set to OSPEEDRy[1:0] = 10
- Capacitive load C = 30 pF
- Measurement points are done at CMOS levels: $0.5V_{DD}$.

Refer to Section *Section 5.3.16: I/O port characteristics* for more details on the input/output characteristics.

Table 60. USB HS DC electrical characteristics

Symbol		**Parameter**	**Min.(1)**	**Max.(1)**	**Unit**
Input level	V_{DD}	USB OTG HS operating voltage	2.7	3.6	V

1. All the voltages are measured from the local ground potential.

Table 61. USB HS clock timing parameters(1)

Parameter		**Symbol**	**Min**	**Nominal**	**Max**	**Unit**
f_{HCLK} value to guarantee proper operation of USB HS interface		-	30	-	-	MHz
Frequency (first transition)	8-bit ±10%	F_{START_8BIT}	54	60	66	MHz

Equation 1: R_{AIN} max formula

$$R_{AIN} = \frac{(k - 0.5)}{f_{ADC} \times C_{ADC} \times \ln(2^{N+2})} - R_{ADC}$$

The formula above (*Equation 1*) is used to determine the maximum external impedance allowed for an error below 1/4 of LSB. N = 12 (from 12-bit resolution) and k is the number of sampling periods defined in the ADC_SMPR1 register.

Table 68. ADC accuracy at f_{ADC} = 30 MHz

Symbol	Parameter	Test conditions	Typ	Max(1)	Unit
ET	Total unadjusted error	f_{PCLK2} = 60 MHz, f_{ADC} = 30 MHz, R_{AIN} < 10 kΩ, V_{DDA} = 1.8(2) to 3.6 V	±2	±5	LSB
EO	Offset error		±1.5	±2.5	
EG	Gain error		±1.5	±3	
ED	Differential linearity error		±1	±2	
EL	Integral linearity error		±1.5	±3	

1. Guaranteed by characterization.
2. V_{DD}/V_{DDA} minimum value of 1.7 V is obtained when the device operates in reduced temperature range, and with the use of an external power supply supervisor (refer to *Section : Internal reset OFF*).

Note: ADC accuracy vs. negative injection current: injecting a negative current on any analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to analog pins which may potentially inject negative currents.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $SI_{INJ(PIN)}$ in Section 5.3.16 does not affect the ADC accuracy.

Figure 56. Asynchronous multiplexed PSRAM/NOR read waveforms

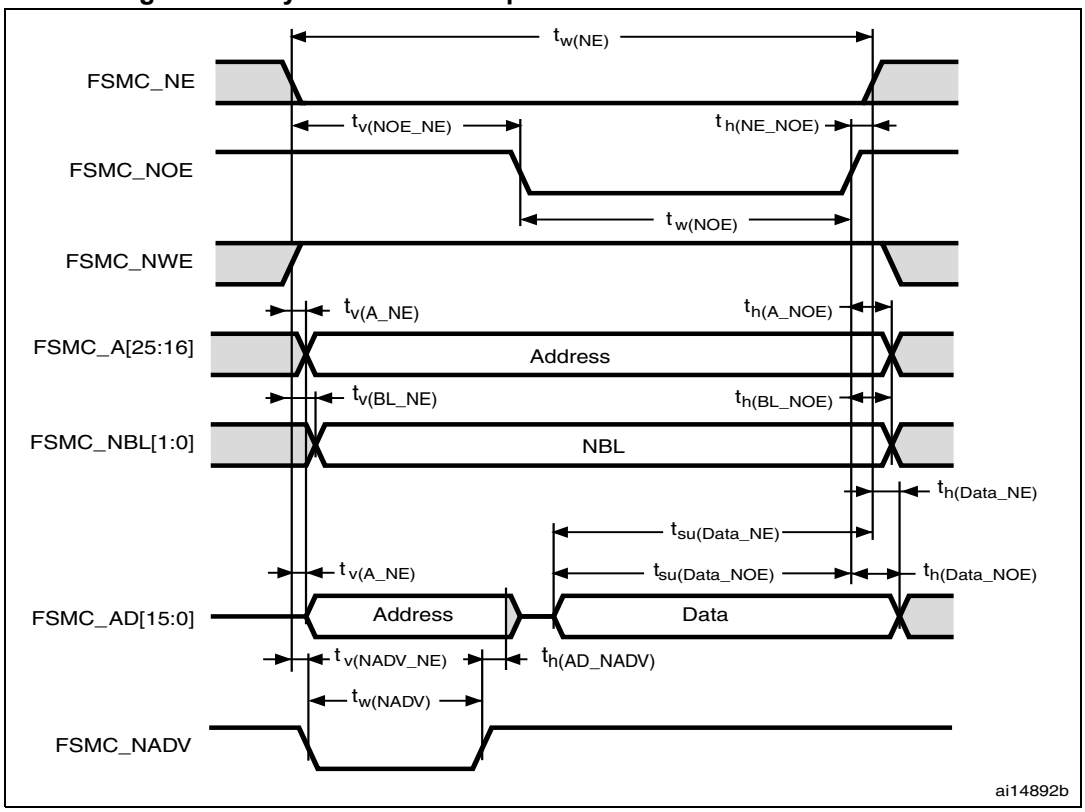


Table 77. Asynchronous multiplexed PSRAM/NOR read timings(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{w(NE)}$	FSMC_NE low time	$3T_{HCLK}-1$	$3T_{HCLK}+1$	ns
$t_{v(NOE\_NE)}$	FSMC_NEx low to FSMC_NOE low	$2T_{HCLK}-0.5$	$2T_{HCLK}+0.5$	ns
$t_{w(NOE)}$	FSMC_NOE low time	$T_{HCLK}-1$	$T_{HCLK}+1$	ns
$t_{h(NE\_NOE)}$	FSMC_NOE high to FSMC_NE high hold time	0	-	ns
$t_{v(A\_NE)}$	FSMC_NEx low to FSMC_A valid	-	3	ns
$t_{v(NADV\_NE)}$	FSMC_NEx low to FSMC_NADV low	1	2	ns
$t_{w(NADV)}$	FSMC_NADV low time	$T_{HCLK}-2$	$T_{HCLK}+1$	ns
$t_{h(AD\_NADV)}$	FSMC_AD(adress) valid hold time after FSMC_NADV high)	T_{HCLK}	-	ns
$t_{h(A\_NOE)}$	Address hold time after FSMC_NOE high	$T_{HCLK}-1$	-	ns
$t_{h(BL\_NOE)}$	FSMC_BL time after FSMC_NOE high	0	-	ns
$t_{v(BL\_NE)}$	FSMC_NEx low to FSMC_BL valid	-	2	ns
$t_{su(Data\_NE)}$	Data to FSMC_NEx high setup time	$T_{HCLK}+4$	-	ns
$t_{su(Data\_NOE)}$	Data to FSMC_NOE high setup time	$T_{HCLK}+4$	-	ns
$t_{h(Data\_NE)}$	Data hold time after FSMC_NEx high	0	-	ns
$t_{h(Data\_NOE)}$	Data hold time after FSMC_NOE high	0	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization.

Figure 67. PC Card/CompactFlash controller waveforms for I/O space write access

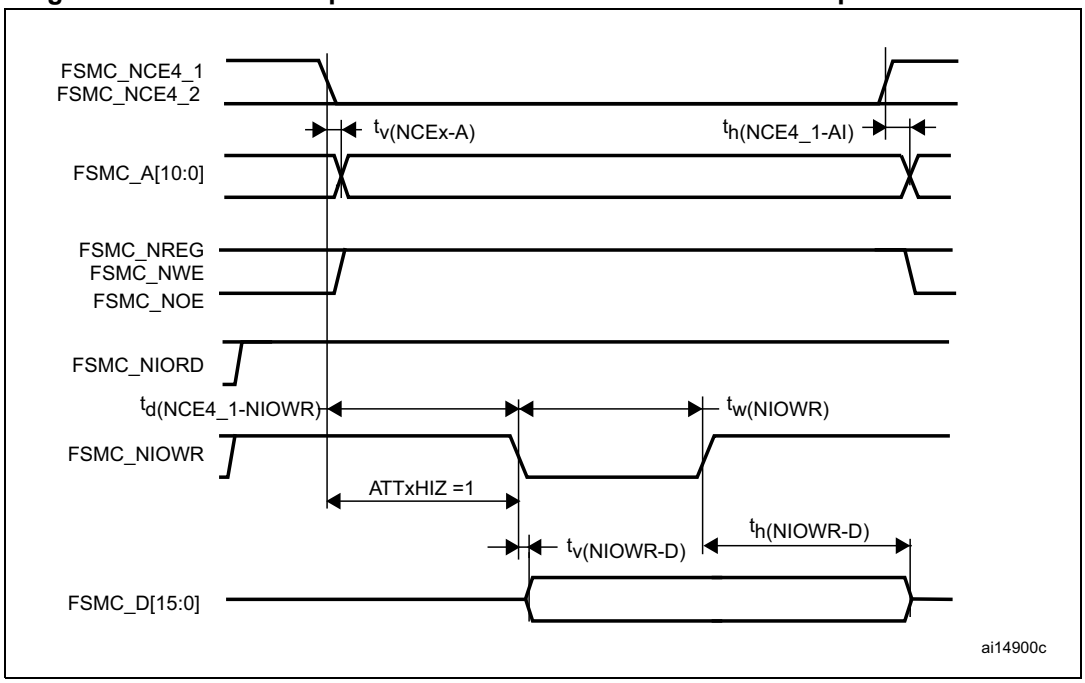


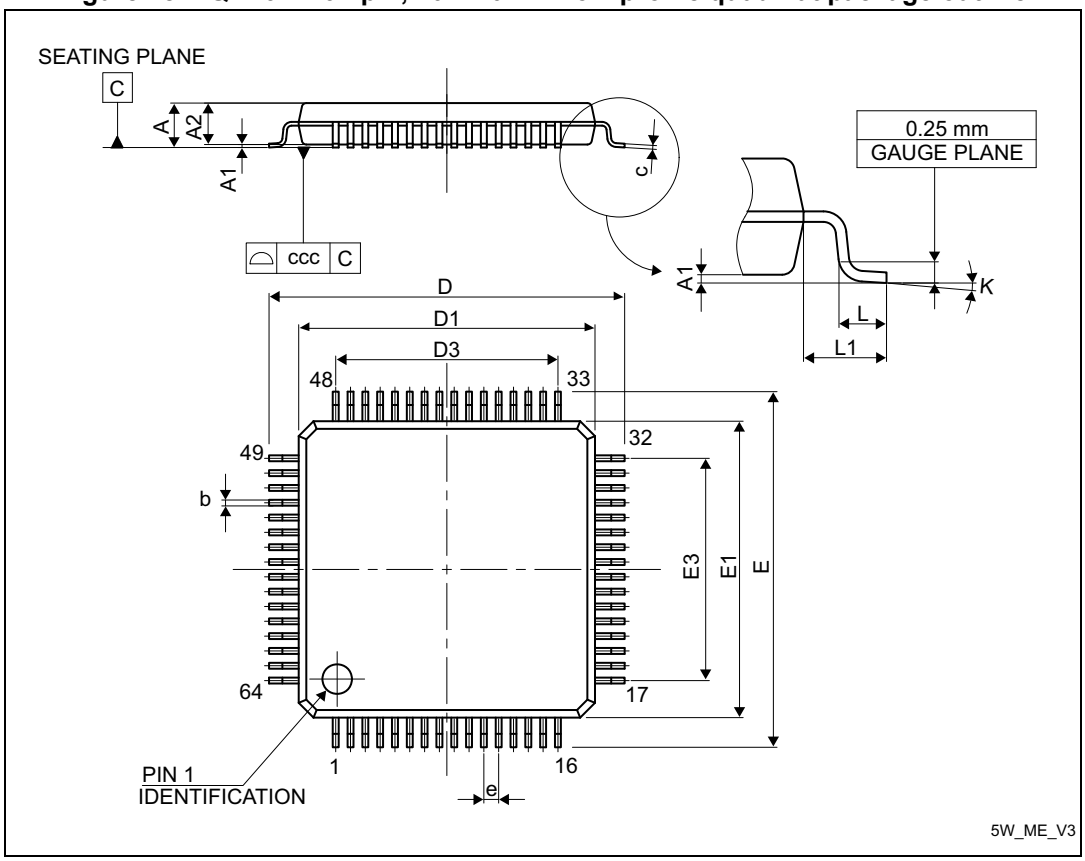
Table 83. Switching characteristics for PC Card/CF read and write cycles in attribute/common space(1)(2)

Symbol	Parameter	Min	Max	Unit
$t_{v(NCEx-A)}$	FSMC_Ncex low to FSMC_Ay valid	-	0	ns
$t_{h(NCEx\_AI)}$	FSMC_NCEx high to FSMC_Ax invalid	4	-	ns
$t_{d(NREG-NCEx)}$	FSMC_NCEx low to FSMC_NREG valid	-	3.5	ns
$t_{h(NCEx-NREG)}$	FSMC_NCEx high to FSMC_NREG invalid	T_{HCLK}+4	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	$5T_{HCLK}$+0.5	ns
$t_{d(NCEx-NOE)}$	FSMC_NCEx low to FSMC_NOE low	-	$5T_{HCLK}$ +0.5	ns
$t_{w(NOE)}$	FSMC_NOE low width	$8T_{HCLK}$–1	$8T_{HCLK}$+1	ns
$t_{d(NOE\_NCEx)}$	FSMC_NOE high to FSMC_NCEx high	$5T_{HCLK}$+2.5	-	ns
$t_{su\ (D-NOE)}$	FSMC_D[15:0] valid data before FSMC_NOE high	4.5	-	ns
$t_{h(N0E-D)}$	FSMC_N0E high to FSMC_D[15:0] invalid	3	-	ns
$t_{w(NWE)}$	FSMC_NWE low width	$8T_{HCLK}$–0.5	$8T_{HCLK}$+ 3	ns
$t_{d(NWE\_NCEx)}$	FSMC_NWE high to FSMC_NCEx high	$5T_{HCLK}$–1	-	ns
$t_{d(NCEx-NWE)}$	FSMC_NCEx low to FSMC_NWE low	-	$5T_{HCLK}$+ 1	ns
$t_{v(NWE-D)}$	FSMC_NWE low to FSMC_D[15:0] valid	-	0	ns
t_h (NWE-D)	FSMC_NWE high to FSMC_D[15:0] invalid	$8T_{HCLK}$ –1	-	ns
t_d (D-NWE)	FSMC_D[15:0] valid before FSMC_NWE high	$13T_{HCLK}$ –1	-	ns

1. C_L = 30 pF.
2. Guaranteed by characterization.

6.2 LQFP64 package information

Figure 78. LQFP64 – 64-pin, 10 x 10 mm low-profile quad flat package outline



1. Drawing is not to scale.

Table 92. LQFP64 – 64-pin 10 x 10 mm low-profile quad flat package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	-	12.000	-	-	0.4724	-
D1	-	10.000	-	-	0.3937	-
D3	-	7.500	-	-	0.2953	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-

Table 95. UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data (continued)

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
eee	-	-	0.150	-	-	0.0059
fff	-	-	0.050	-	-	0.0020

1. Values in inches are converted from mm and rounded to 4 decimal digits.

Figure 88. UFBGA176+25 - 201-ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array recommended footprint

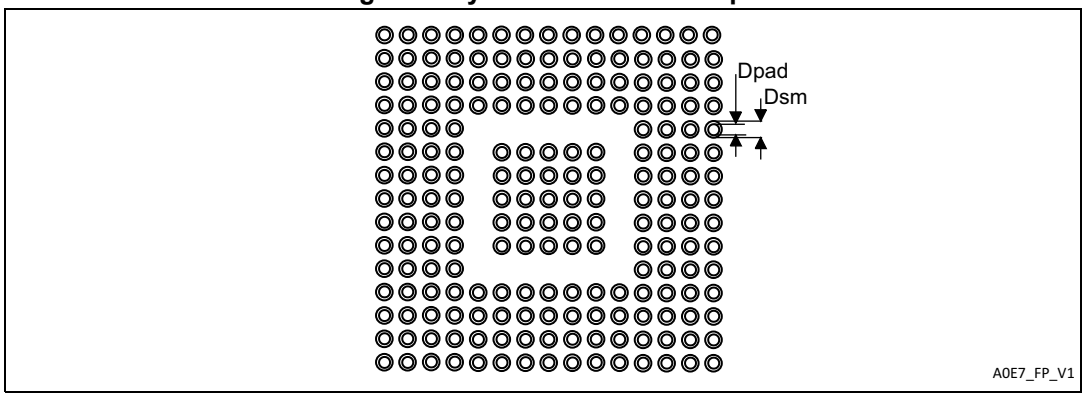


Table 96. UFBGA176+2 recommended PCB design rules (0.65 mm pitch BGA)

Dimension	Recommended values
Pitch	0.65
Dpad	0.300 mm
Dsm	0.400 mm typ. (depends on the soldermask registration tolerance)

Note: Non solder mask defined (NSMD) pads are recommended.

4 to 6 mils solder paste screen printing process.

Stencil opening is 0.300 mm.

Stencil thickness is between 0.100 mm and 0.125 mm.

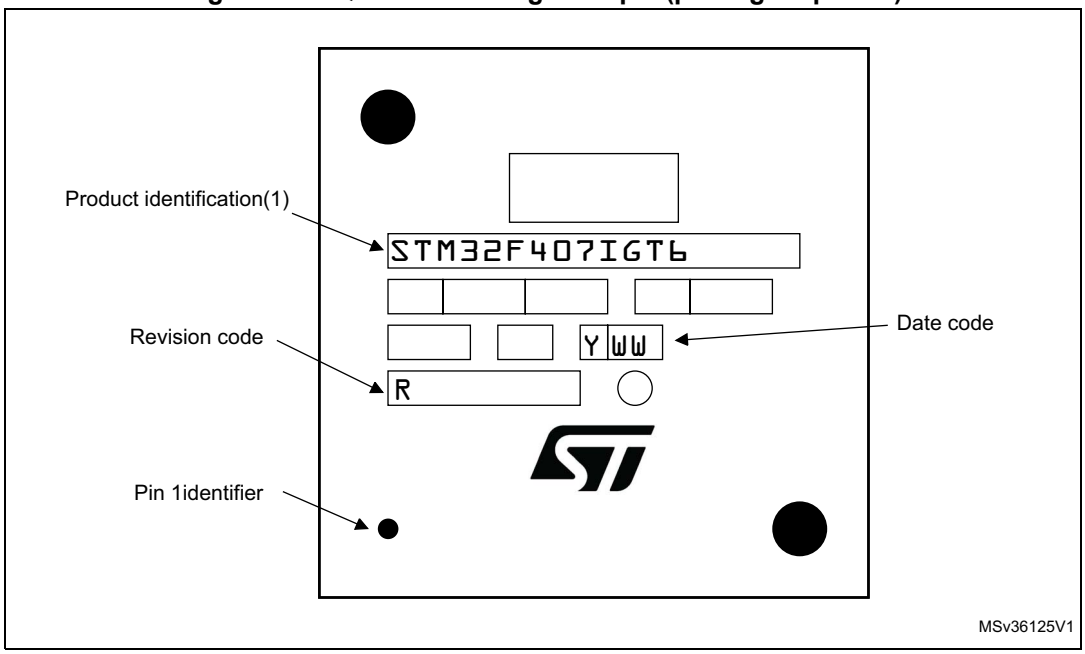
Pad trace width is 0.100 mm.

Device marking for LQFP176

The following figure gives an example of topside marking and pin 1 position identifier location.

Other optional marking or inset/upset marks, which depend on supply chain operations, are not indicated below.

Figure 92. LQFP176 marking example (package top view)



1. Parts marked as “ES”, “E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

Table 100. Document revision history (continued)

Date	Revision	Changes
04-Jun-2013	4 (continued)	Updated *Table 64: Dynamic characteristics: Eternity MAC signals for SMI*. Updated *Table 66: Dynamic characteristics: Ethernet MAC signals for MII*. Updated *Table 79: Synchronous multiplexed NOR/PSRAM read timings*. Updated *Table 80: Synchronous multiplexed PSRAM write timings*. Updated *Table 81: Synchronous non-multiplexed NOR/PSRAM read timings*. Updated *Table 82: Synchronous non-multiplexed PSRAM write timings*. Updated *Section 5.3.27: Camera interface (DCMI) timing specifications* including *Table 87: DCMI characteristics* and addition of *Figure 72: DCMI timing diagram*. Updated *Section 5.3.28: SD/SDIO MMC card host interface (SDIO) characteristics* including *Table 88*. Updated *Chapter Figure 9.*

Table 100. Document revision history (continued)

Date	Revision	Changes
22-Oct-2015	6	In the whole document, updated notes related to values guaranteed by design or by characterization. Updated *Table 34: HSI oscillator characteristics*. Changed f_{VCO_OUT} minimum value and VCO freq to 100 MHz in *Table 36: Main PLL characteristics* and *Table 37: PLLI2S (audio PLL) characteristics*. Updated *Figure 39: SPI timing diagram - slave mode and CPHA = 0*. Updated *Figure 53: 12-bit buffered /non-buffered DAC*. Removed note 1 related to better performance using a restricted V_{DD} range in *Table 68: ADC accuracy at fADC = 30 MHz*. Upated *Figure 84: LQFP144 - 144-pin, 20 x 20 mm low-profile quad flat package outline*. Updated *Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline* and *Table 95: UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data*.
16-Mar-2016	7	Updated *Figure 2: Compatible board design STM32F10xx/STM32F2/STM32F40xxx for LQFP100 package*. Updated $\|V_{SSX}-V_{SS}\|$ in *Table 11: Voltage characteristics* to add V_{REF+} Added V_{REF-}in *Table 67: ADC characteristics*. Updated *Table 90: WLCSP90 - 4.223 x 3.969 mm, 0.400 mm pitch wafer level chip scale package mechanical data*.
09-Sep-2016	8	Remove note 1 below *Figure 5: STM32F40xxx block diagram*. Updated definition of stresses above maximum ratings in *Section 5.2: Absolute maximum ratings*. Updated $t_{h(NSS)}$) in *Figure 39: SPI timing diagram - slave mode and CPHA = 0Figure* and *Figure 40: SPI timing diagram - slave mode and CPHA = 1*. Added note related to optional marking and inset/upset marks in all package marking sections. Updated *Figure 87: UFBGA176+25 ball, 10 x 10 mm, 0.65 mm pitch, ultra fine pitch ball grid array package outline* and *Table 95: UFBGA176+25 ball, 10 × 10 × 0.65 mm pitch, ultra thin fine pitch ball grid array mechanical data*.